

60V NPN MEDIUM POWER TRANSISTOR IN SOT223

Features

- BV_{CEO} > 60V
- I_C = 6A High Continuous Collector Current
- I_{CM} = 20A Peak Pulse Current
- Low Saturation Voltage V_{CE(SAT)} < 100mV @ 1A
- R_{CE(SAT)} = 44mΩ for a Low Equivalent On-Resistance
- h_{FE} Specified Up to 10A for a High Gain Hold Up
- Complementary PNP Type: FZT951
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

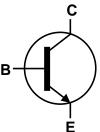
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208
- Weight: 0.112 grams (Approximate)

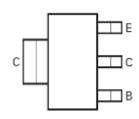




Top View



Device Symbol



Top View Pin-Out

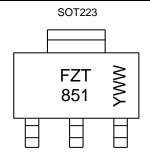
Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
FZT851TA	AEC-Q101	FZT851	7	12	1,000
FZT851QTA	Automotive	FZT851	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



FZT 851 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01–53)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	150	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	7	V
Continuous Collector Current	Ic	6	A
Peak Pulse Current	I _{CM}	20	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 6)		3.0 24	W mW/°C	
Linear Derating Factor	(Note 7)	P _D	1.6 12.8		
Thermal Desigtance Junction to Ambient	(Note 6)	$R_{\theta JA}$	42		
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	78	°C/W	
Thermal Resistance Junction to Lead (Note 8)		$R_{ heta JL}$	8.8		
Operating and Storage Temperature Range	T _{J.} T _{STG}	-55 to +150	°C		

ESD Ratings (Note 9)

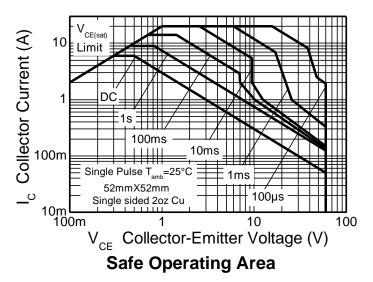
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

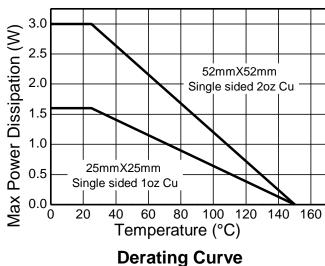
Notes:

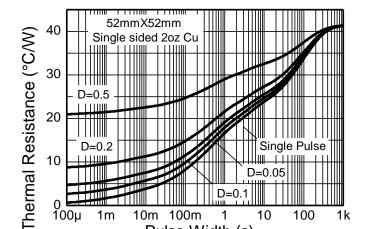
- 6. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
- 7. Same as Note 6, except the device is mounted on 25mm x 25mm 1oz copper.
- 8. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information







Single Pulse T_{amb}=25°C Max Power Dissipation (W) 52mmX52mm Single sided 2oz Cu 1 └── 100µ

10m 100m

1m

Transient Thermal Impedance

Pulse Width (s)

Pulse Power Dissipation

Pulse Width (s)

10

100

1k

100



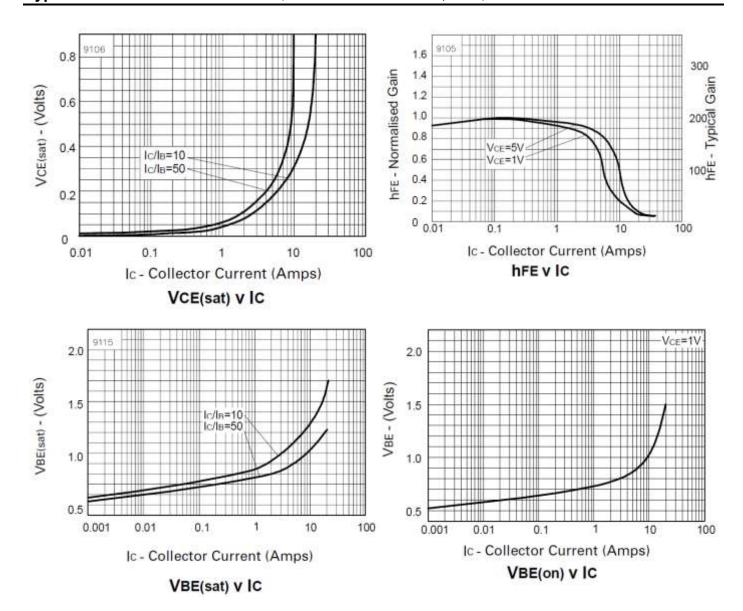
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	150	220	_	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage	BV _{CER}	150	220	_	V	$I_C = 1\mu A, R_B \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	60	85	_	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.1	_	V	$I_E = 100 \mu A$
Collector Cut-Off Current	I _{CBO}	_	<1 -	50 1	nΑ μΑ	V _{CB} = 120V V _{CB} = 120V, T _A = +100°C
Collector Cut-Off Current	I _{CER}	_	<1 —	50 1	nΑ μΑ	$V_{CE} = 120V, R_B \le 1k\Omega$ $V_{CE} = 120V, T_A = +100^{\circ}C$
Emitter Cut-Off Current	I _{EBO}	_	<1	10	nA	V _{EB} = 6V
	hFE	100	200	_		I _C = 10mA, V _{CE} = 1V
DC Current Gain (Note 10)		100	200	300		I _C = 2A, V _{CE} = 1V
DC Current Gain (Note 10)		75	120	_		I _C = 5A, V _{CE} = 1V
		25	50	_		$I_C = 10A, V_{CE} = 1V$
		_	_	50	m∨	$I_C = 100 \text{mA}, I_B = 5 \text{mA}$
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(SAT)}	_	_	100		$I_C = 1A, I_B = 50mA$
Collector-Entitler Saturation Voltage (Note 10)		_	_	170	IIIV	$I_C = 2A$, $I_B = 50mA$
	<u>[</u>	_	_	375		$I_C = 6A, I_B = 300mA$
Base-Emitter Saturation Voltage (Note 10)	$V_{BE(SAT)}$	_	_	1,200	mV	$I_C = 6A, I_B = 300mA$
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(ON)}	_	_	1,150	mV	I _C = 6A, V _{CE} = 1V
Current Gain-Bandwidth Product (Note 10)	f _T	_	130	_	MHz	I _C = 100mA, V _{CE} = 10V, f = 50MHz
Output Capacitance	Сово	_	45	_	pF	$V_{CB} = 10V$, $f = 1MHz$
Switching Times	t _{ON}	_	45	_	ns	I _C = 1A, V _{CC} = 10V,
Owitering Tilles	toff	_	1,100	_	110	$I_{B1} = -I_{B2} = 100 \text{mA}$

Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



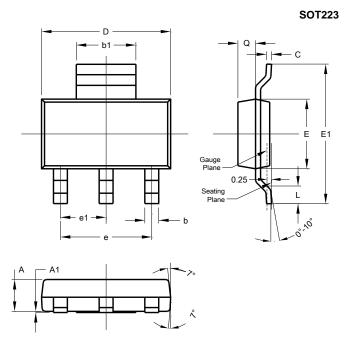
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)





Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

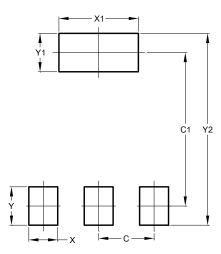


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
Х	1.20		
X1	3.30		
Y	1.60		
Y1	1.60		
Y2	8.00		

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